

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

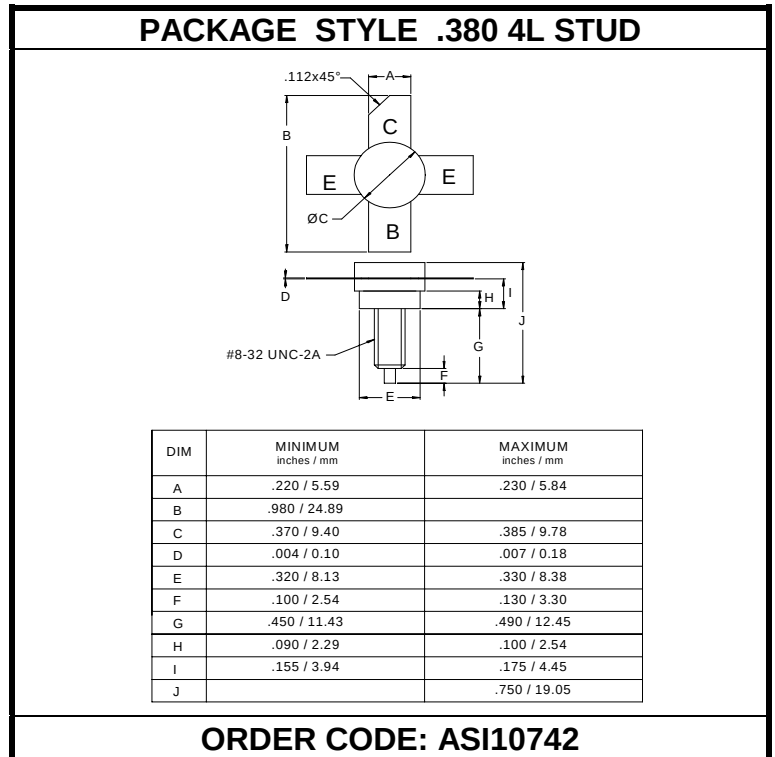
The **ASI VMB10-12S** is Designed for 12.5 V, Medium Band Class C Application.

FEATURES:

- Common Emitter
- $P_G = 13$ dB at 10 W/88 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	20 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	5.0 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 15$ mA		18			V
BV_{CES}	$I_C = 50$ mA		36			V
BV_{EBO}	$I_E = 2.5$ mA		4.0			V
I_{CBO}	$V_{CB} = 12.5$ V				1.0	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 250$ mA	5.0		200	---
C_{OB}	$V_{CB} = 12.5$ V	$f = 1.0$ MHz			65	pF
P_G η_c	$V_{CE} = 12.5$ V	$P_{OUT} = 10$ W $f = 88$ MHz	13	60		dB %